

BGD704

750 MHz, 20 dB gain power doubler amplifier

Rev. 8 — 28 September 2010

Product data sheet

1. Product profile

1.1 General description

Hybrid amplifier module in a SOT115J package operating with a voltage supply of 24 V (DC).

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability

1.3 Applications

CATV systems in the frequency range of 40 MHz to 750 MHz

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz	19.5	20	20.5	dB
		f = 750 MHz	20	21	-	dB
I _{tot}	total current consumption (DC)	V _B = 24 V	-	425	435	mA



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2. Pinning information

Table 2. Pinning

	3	
Pin	Description	Simplified outline Graphic symbol
1	input	
2	common	1 3 5 7 9
3	common	
5	+V _B	12 3 7 8
7	common	sym095
8	common	
9	output	

3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BGD704	-	rectangular single-ended package; aluminium flange; 2 vertical mounting holes; $2 \times 6-32$ UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads	SOT115J			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_i	RF input voltage		-	65	dBmV
T _{stg}	storage temperature		-40	+100	°C
T _{mb}	mounting base operating temperature		-20	+100	°C

5. Characteristics

Table 5. Characteristics

Bandwidth 40 MHz to 750 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75 \Omega$.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G_p	power gain	f = 50 MHz	19.5	20	20.5	dB
		f = 750 MHz	20	21	-	dB
SL	slope cable equivalent	f = 40 MHz to 750 MHz	0	1	2	dB
FL	flatness of frequency response	f = 40 MHz to 750 MHz	-	±0.2	±0.5	dB
s ₁₁	input return losses	f = 40 MHz to 80 MHz	20	31	-	dB
		f = 80 MHz to 160 MHz	19	29	-	dB
		f = 160 MHz to 320 MHz	18	25	-	dB
		f = 320 MHz to 640 MHz	17	21	-	dB
		f = 640 MHz to 750 MHz	16	21	-	dB

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 Table 5.
 Characteristics ...continued

Bandwidth 40 MHz to 750 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75 \Omega$.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
S ₂₂	output return losses	f = 40 MHz to 80 MHz	20	26	-	dB
		f = 80 MHz to 160 MHz	19	27	-	dB
		f = 160 MHz to 320 MHz	18	26	-	dB
		f = 320 MHz to 640 MHz	17	24	-	dB
		f = 640 MHz to 750 MHz	16	23	-	dB
s ₂₁	phase response	f = 50 MHz	-45	-	+45	deg
СТВ	composite triple beat	110 channels flat; $V_o = 44 \text{ dBmV}$; measured at 745.25 MHz	-	-58	–57	dB
X_{mod}	cross modulation	110 channels flat; $V_0 = 44 \text{ dBmV}$; measured at 55.25 MHz	-	-63	-61	dB
CSO	composite second order distortion	110 channels flat; $V_0 = 44 \text{ dBmV}$; measured at 746.5 MHz	-	-61	-56	dB
d_2	second order distortion		<u>[1]</u> -	−75	-66	dB
Vo	output voltage	$d_{im} = -60 \text{ dB}$	^[2] 60.5	63.5	-	dBmV
F	noise figure	f = 50 MHz	-	4.5	5	dB
		f = 450 MHz	-	-	6.5	dB
		f = 550 MHz	-	-	7	dB
		f = 600 MHz	-	-	7	dB
		f = 750 MHz	-	6.5	8.5	dB
I _{tot}	total current consumption (DC)		[3]	425	435	mA

^[1] $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 691.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 746.5$ MHz.

Table 6. Characteristics

Bandwidth 40 MHz to 600 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75 \Omega$.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz	19.5	20	20.5	dB
		f = 600 MHz	20	20.7	-	dB
SL	slope cable equivalent	f = 40 MHz to 600 MHz	0	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 600 MHz	-	-	±0.3	dB
s ₁₁	s ₁₁ input return losses	f = 40 MHz to 80 MHz	20	31	-	dB
		f = 80 MHz to 160 MHz	19	29	-	dB
		f = 160 MHz to 320 MHz	18	25	-	dB
		f = 320 MHz to 600 MHz	17	21	-	dB
s ₂₂	output return losses	f = 40 MHz to 80 MHz	20	26	-	dB
		f = 80 MHz to 160 MHz	19	27	-	dB
		f = 160 MHz to 320 MHz	18	26	-	dB
		f = 320 MHz to 600 MHz	17	24	-	dB
S ₂₁	phase response	f = 50 MHz	-45	-	+45	deg

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^[2] Measure according to DIN45004B; f_p = 740.25 MHz; V_p = V_o ; f_q = 747.25 MHz; V_q = V_o - 6 dB; f_r = 749.25 MHz; V_r = V_o - 6 dB; measured at f_p + f_q - f_r = 738.25 MHz.

^[3] The module normally operates at $V_B = 24 \text{ V}$, but is able to withstand supply transients up to 30 V.

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 Table 6.
 Characteristics ...continued

Bandwidth 40 MHz to 600 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75 \Omega$.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
СТВ	composite triple beat	85 channels flat; V_0 = 44 dBmV; measured at 595.25 MHz	-	-65	-64	dB
X_{mod}	cross modulation	85 channels flat; V_0 = 44 dBmV; measured at 55.25 MHz	-	-65	-64	dB
CSO	composite second order distortion	85 channels flat; V_0 = 44 dBmV; measured at 596.5 MHz	-	-66	-58	dB
d_2	second order distortion		<u>[1]</u> _	-	-68	dB
V _o	output voltage	$d_{im} = -60 \text{ dB}$	^[2] 63	-	-	dBmV
F	noise figure	see <u>Table 5</u>	-	-	-	dBmV
I _{tot}	total current consumption (DC)		[3]	425	435	mΑ

^[1] $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 541.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 596.5$ MHz.

Table 7. Characteristics

Bandwidth 40 MHz to 550 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75 \Omega$.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Gp	power gain	f = 50 MHz		19.5	20	20.5	dB
		f = 550 MHz		20	20.6	-	dB
SL	slope cable equivalent	f = 40 MHz to 550 MHz		0	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 550 MHz		-	-	±0.3	dB
s ₁₁	input return losses	f = 40 MHz to 80 MHz		20	31	-	dB
		f = 80 MHz to 160 MHz		19	29	-	dB
		f = 160 MHz to 320 MHz		18	25	-	dB
		f = 320 MHz to 550 MHz		17	21	-	dB
s ₂₂ output return losses	f = 40 MHz to 80 MHz		20	26	-	dB	
		f = 80 MHz to 160 MHz		19	27	-	dB
		f = 160 MHz to 320 MHz		18	26	-	dB
		f = 320 MHz to 550 MHz		17	24	-	dB
s ₂₁	phase response	f = 50 MHz		-45	-	+45	deg
СТВ	composite triple beat	77 channels flat; V_0 = 44 dBmV; measured at 547.25 MHz		-	-67	-66	dB
X_{mod}	cross modulation	77 channels flat; V_o = 44 dBmV; measured at 55.25 MHz		-	-67	-66	dB
CSO	composite second order distortion	77 channels flat; V_o = 44 dBmV; measured at 548.5 MHz		-	-67	-60	dB
d_2	second order distortion		[1]	-	-	-70	dB
Vo	output voltage	$d_{im} = -60 \text{ dB}$	[2]	63.5	-	-	dBmV
F	noise figure	see <u>Table 5</u>		-	-	-	dB
I _{tot}	total current consumption (DC)		[3]	-	425	435	mA

^[1] $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 493.25$ MHz; $V_q = 44$ dBmV; measured at $f_p + f_q = 548.5$ MHz.

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^[2] Measured according to DIN45004B; f_p = 590.25 MHz; V_p = V_o ; f_q = 597.25 MHz; V_q = V_o - 6 dB; f_r = 599.25 MHz; V_r = V_o - 6 dB; measured at f_p + f_q - f_r = 588.25 MHz.

^[3] The module normally operates at $V_B = 24 \text{ V}$, but is able to withstand supply transients up to 30 V.

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- [2] Measure according to DIN45004B; f_p = 540.25 MHz; V_p = V_o ; f_q = 547.25 MHz; V_q = V_o 6 dB; f_r = 549.25 MHz; V_r = V_o 6 dB; measured at f_p + f_q f_r = 538.25 MHz.
- [3] The module normally operates at $V_B = 24 \text{ V}$, but is able to withstand supply transients up to 30 V.

Table 8. Characteristics Bandwidth 40 MHz to 450 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75 \Omega$.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
G_p	power gain	f = 50 MHz		19.5	20	20.5	dB
		f = 450 MHz		20	20.6	-	dB
SL	slope cable equivalent	f = 40 MHz to 450 MHz		0	-	2	dB
FL	flatness of frequency response	f = 40 MHz to 450 MHz		-	-	±0.3	dB
S ₁₁	input return losses	f = 40 MHz to 80 MHz		20	31	-	dB
		f = 80 MHz to 160 MHz		19	29	-	dB
		f = 160 MHz to 320 MHz		18	25	-	dB
		f = 320 MHz to 450 MHz		17	21	-	dB
S ₂₂	s ₂₂ output return losses	f = 40 MHz to 80 MHz		20	26	-	dB
		f = 80 MHz to 160 MHz		19	27	-	dB
		f = 160 MHz to 320 MHz		18	26	-	dB
		f = 320 MHz to 450 MHz		17	24	-	dB
S ₂₁	phase response	f = 50 MHz		-45	-	+45	deg
СТВ	composite triple beat	60 channels flat; V_o = 46 dBmV; measured at 445.25 MHz		-	-	-67	dB
X_{mod}	cross modulation	60 channels flat; V_o = 46 dBmV; measured at 55.25 MHz		-	-	-64	dB
CSO	composite second order distortion	60 channels flat; V_o = 46 dBmV; measured at 446.5 MHz		-	-	-63	dB
d_2	second order distortion		[1]	-	-	-73	dB
Vo	output voltage	$d_{im} = -60 \text{ dB}$	[2]	66	-	-	dBmV
F	noise figure	see <u>Table 5</u>		-	-	-	dB
I _{tot}	total current consumption (DC)		[3]	-	425	435	mA

^[1] $f_p = 55.25$ MHz; $V_p = 44$ dBmV; $f_q = 391.25$ MHz; $V_q = 46$ dBmV; measured at $f_p + f_q = 446.5$ MHz.

^[2] Measured according to DIN45004B; $f_p = 440.25$ MHz; $V_p = V_o$; $f_q = 447.25$ MHz; $V_q = V_o - 6$ dB; $f_r = 449.25$ MHz; $V_r = V_o - 6$ dB; measured at $f_p + f_q - f_r = 438.25$ MHz.

^[3] The module normally operates at $V_B = 24 \text{ V}$, but is able to withstand supply transients up to 30 V.

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6. Package outline

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J

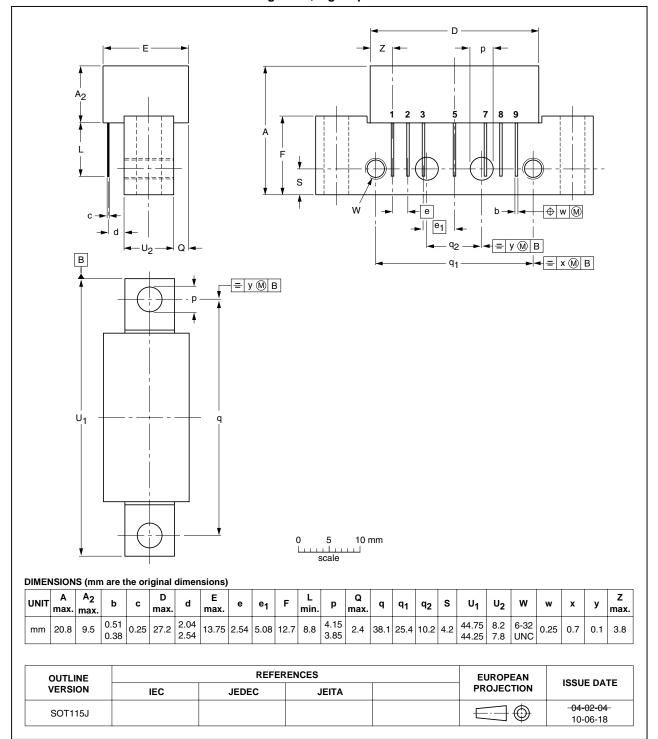


Fig 1. Package outline SOT115J

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7. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGD704 v.8	20100928	Product data sheet	-	BGD704 v.7
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity
	 Legal texts 	have been adapted to the ne	ew company name whe	ere appropriate.
	 Package ou 	ıtline drawings have been up	dated to the latest vers	sion.
BGD704 v.7 (9397 750 14776)	20050401	Product data sheet	-	BGD704 v.6
BGD704 v.6 (9397 750 09027)	20011102	Product specification	-	BGD704 v.5
BGD704 v.5 (9397 750 08846)	20011029	Product specification	-	BGD704 v.4
BGD704 v.4 (9397 750 05295)	19990322	Product specification	-	BGD704 v.3
BGD704 v.3 (9397 750 01971)	19970402	Product specification	-	BGD704 v.2
BGD704 v.2 (9397 750 01392)	19961220	Product specification	-	-

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8. Legal information

8.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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